Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting Information

Threshold voltage tuning of IGZTO thin-film transistors deposited by RF sputtering for high-resolution flexible displays using deep ultraviolet light.

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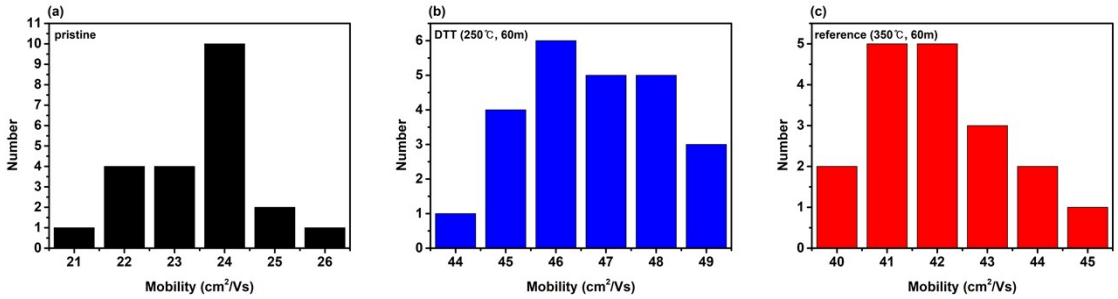

Figure S1. Mobility distributions of TFT devices with various annealing treatments applied to IGZTO thin film. (a)pristine IGZTO TFT, (b)DTT (250ºC, 60m) IGZTO TFT, (c)reference (350ºC, 60m) IGZTO TFT. At least 18 devices were fabricated and evaluated.

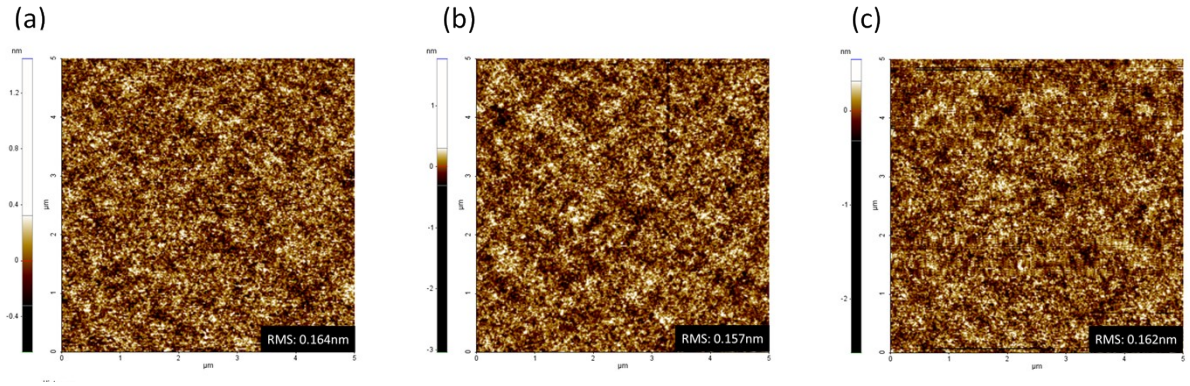

Figure S2. AFM images of (a) pristine, (b) DTT (250 ℃, 60 min), and (c) reference (350 ℃, 60 min), respectively.

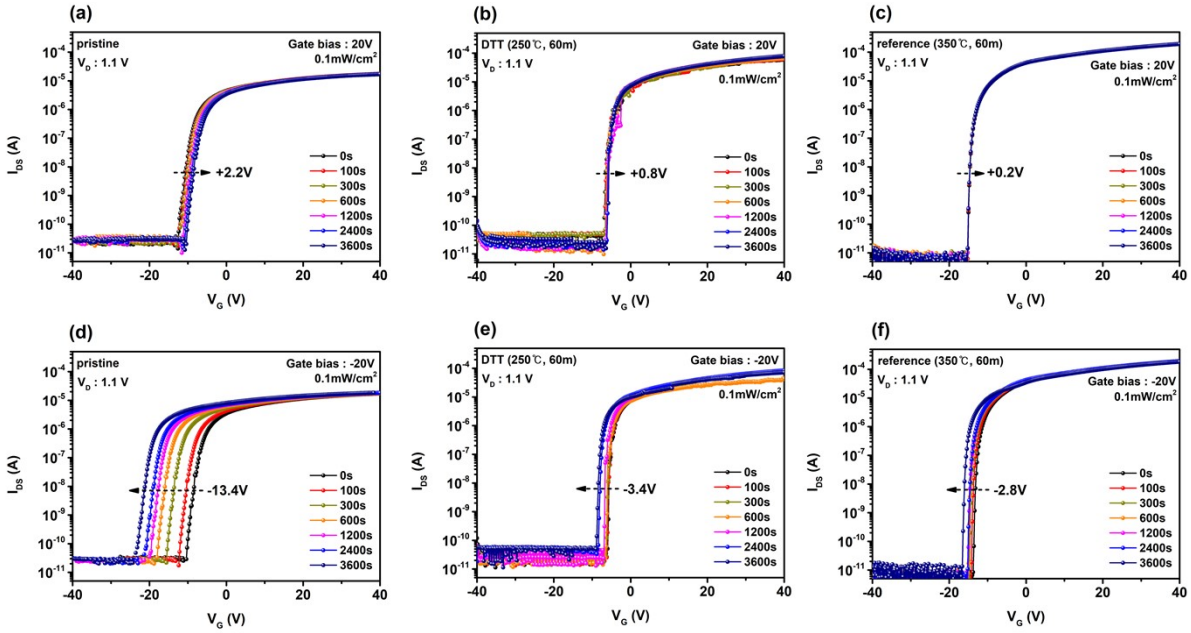

Figure S3. Positive bias illumination stress and negative bias illumination stress of (a)(d) pristine, (b)(e) DTT (250 ℃, 60 min), and (c)(f) reference (350 ℃, 60 min), respectively.